

Technical Data Green Products

Data Sheet N1188, Rev. A

201CNQ035/201CNQ040/201CNQ045/201CNQ050 SCHOTTKY RECTIFIER

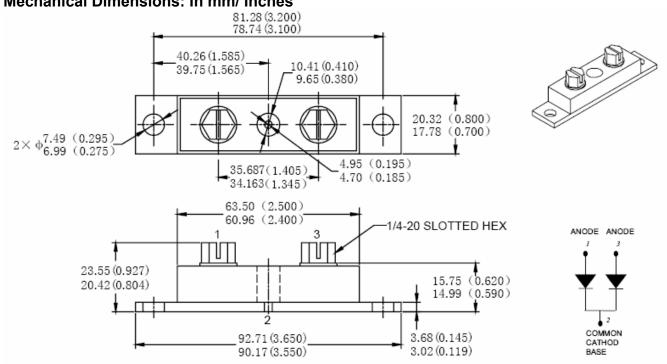
Applications:

- High current switching power supply Plating power supply Free-Wheeling diodes
- Reverse battery protection Converters UPS System Welding

Features:

- 175 °C T_J operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm/ Inches



PRM4 (Non-Isolated)

MARKING, MOLDING RESIN

Marking for 201CNQ035/040/045/050, 1st row SS YYWWL, 2nd row 201CNQ035/040/045/050 Where YY is the manufacture year WW is the manufacture week code

L is the wafer's Lot Number

Molding resin

Epoxy resin UL:94V-0

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201CNQ SERIES

Green Products **Technical Data**

Data Sheet N1188, Rev. A **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.		Units
Peak Inverse Voltage	V_{RWM}	-	35 201CNQ035		V
			40	201CNQ040	
			45	201CNQ045	
			50	201CNQ050	
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =121°C,	100	per leg	Α
		rectangular wave form	200	per device	
Max. Peak One Cycle Non-					
Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	3840		Α
Non-Repetitive Avalanche Energy(peg leg)	E _{AS}	T _J =25℃,I _{AS} =20A,L=0.67mH	135		mJ
Repetitive Avalanche Current(peg leg)	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max. V _A =1.5× V _R typical		20	A

Electrical Characteristics:

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Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 100A, Pulse, T _J = 25 °C	0.67	V
		@ 200A, Pulse, T _J = 25 °C	0.81	
	V_{F2}	@ 100A, Pulse, T _J = 125 °C	0.58	V
		@ 200A, Pulse, T _J = 125 °C	0.71	
Max. Reverse Current (per leg) *	I_{R1}	$@V_R = rated V_R T_J = 25 °C$	10	mA
	I _{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	90	mA
Max. Junction Capacitance (per leg)	C _T	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	5200	pF
Typical Series Inductance		Measured lead to lead 5 mm	7.0	nH
(per leg)	ĽS	from package body		
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifi	Units		
Max. Junction Temperature	T_J	-	-55 to	°C		
Max. Storage Temperature	T _{stg}	-	-55 to	°C		
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ heta JC}$	DC operation	0.50		°C/W	
Maximum Thermal Resistance Junction to Case (per package)	$R_{ heta JC}$	DC operation	0.25		°C/W	
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.10		°C/W	
Mounting Torque	Тм	-	Mounting Torque Terminal Torque	24(min) 35(max) 35(min) 46(max)	Kg-cm	
Approximate Weight	wt	-	79		g	
Case Style	PRM4 Non-Isolated					

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0.2

0.3

0.4

0.5

Forward Voltage Drop - V_F (V)

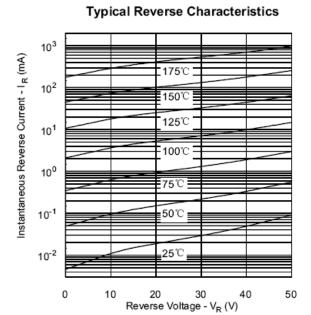
0.6

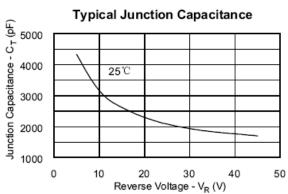
0.7

0.8

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Typical Forward Characteristics 175°C 175°C 125°C 101





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